Silicon NPN Planar, Darlington

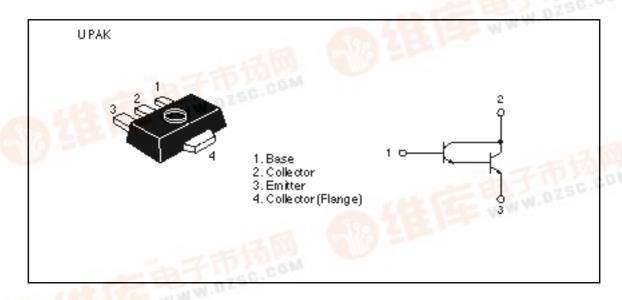
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Application

High gain amplifier

WWW.BZSC

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	40	V
Collector to emitter voltage	V _{CEO}	30	V
Emitter to base voltage	V_{EBO}	10	V
Collector current	I _c	300	mA
Collector peak current	i _{C(peak)} *1	500	mA
Collector power dissipation	P _c *²	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. Pulse 10 ms, Duty cycle 20%

2. Value on the alumina ceramic board (12.5 x 30 x 0.7 mm)

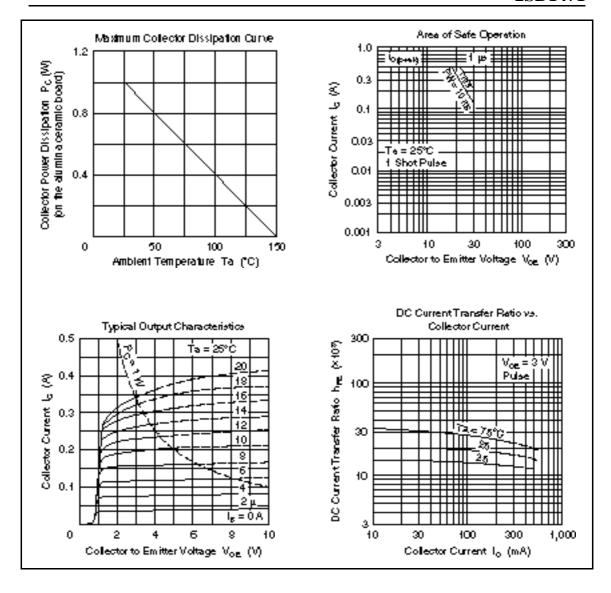
Electrical Characteristics ($Ta = 25^{\circ}C$)

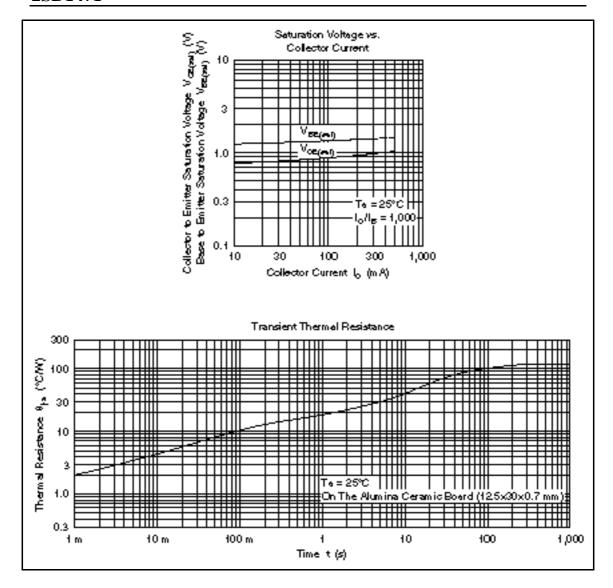
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	40	_	_	V	$I_{c} = 10 \ \mu\text{A}, \ I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	_	_	V	$I_C = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	10	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	1	μΑ	$V_{CB} = 30 \text{ V}, I_{E} = 0$
	I _{CEO}	_	_	10	μΑ	V _{CE} = 24 V, R _{BE} =
DC current transfer ratio	h _{FE1} *1	2000	_	100000)	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}^{*2}$
	h _{FE2} *1	3000	_	_		$V_{CE} = 5 \text{ V}, I_{C} = 100 \text{ mA}^{*2}$
	h _{FE3} *1	3000	_	_		$V_{CE} = 5 \text{ V}, I_{C} = 400 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.5	V	$I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}^{*2}$
Base to emitter saturation voltage	$V_{BE(sat)}$	_	_	2.0	V	$I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}^{*2}$

Notes: 1. The 2SD1471 is grouped by h_{FE} as follows.

Pulse test

Mark	DT	ET
h _{FE1}	2000 to 100000	5000 to 100000
h _{FE2}	3000 min	10000 min
h _{FE3}	3000 min	10000 min





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